

In the Claims:

Marked up version of once amended claim 33:

33. (Once Amended) A composite structure in an IC chip, said composite structure comprising:

- a first metal pad structure comprising a first interconnect metal;
- a first via pad structure below said first metal pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first via metal contacting said first interconnect metal.

Clean version of once amended claim 33:

Sub C1

33. (Once Amended) A composite structure in an IC chip, said composite structure comprising:

- a first metal pad structure comprising a first interconnect metal;
- a first via pad structure below said first metal pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first via metal contacting said first interconnect metal.

DK

Marked up version of once amended claim 45:

45. (Once Amended) A method for fabricating a composite structure in an IC chip, said method comprising steps of:

fabricating a first via pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers;

fabricating a first metal pad structure above said first via pad structure, said first metal pad structure comprising a first interconnect metal, said first interconnect metal contacting at least one of said plurality of segments of said first via metal.

Clean version of once amended claim 45:

45. (Once Amended) A method for fabricating a composite structure in an IC chip, said method comprising steps of:

fabricating a first via pad structure, said first via pad structure comprising a plurality of segments of a first via metal and a first plurality of dielectric fillers;

fabricating a first metal pad structure above said first via pad structure, said first metal pad structure comprising a first interconnect metal, said first interconnect metal contacting at least one of said plurality of segments of said first via metal.

Marked up version of once amended claim 51:

51. (Once Amended) A composite structure in an IC chip, said composite structure comprising:

a first via pad structure comprising a first via metal;
a first metal pad structure below said first via pad structure, said first metal pad structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first interconnect metal contacting said first via metal.

Clean version of once amended claim 51:

SIC 3
51. (Once Amended) A composite structure in an IC chip, said composite structure comprising:
a first via pad structure comprising a first via metal;
a first metal pad structure below said first via pad structure, said first metal pad structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first interconnect metal contacting said first via metal.

BB

Marked up version of once amended claim 62:

62. (Once Amended) A composite structure in an IC chip, said composite structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, said plurality of segments of said first interconnect metal being electrically connected to each other.

Clean version of once amended claim 62:

B4 62. (Once Amended) A composite structure in an IC chip, said composite structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, said plurality of segments of said first interconnect metal being electrically connected to each other.

Please add the following new claims:

Sub C4
--69. A composite structure comprising:

a first via pad structure comprising a first via metal;

a first metal pad structure below said first via pad structure, said first metal pad structure comprising a plurality of segments of a first interconnect metal and a first plurality of dielectric fillers, at least one of said plurality of segments of said first interconnect metal contacting said first via metal;

B5 a second via pad structure below said first metal pad structure, said second via pad structure comprising a plurality of segments of a second via metal and a second plurality of dielectric fillers, at least one of said plurality of segments of said second via metal contacting said first interconnect metal.--

--70. The composite structure of claim 69 wherein said second via metal is selected from the group consisting of copper and tungsten.--

--71. The composite structure of claim 69 wherein said second plurality of dielectric fillers comprise a low-k dielectric.--

cont
B5
--72. The composite structure of claim 71 wherein said low-k dielectric is selected from the group consisting of porous silica, fluorinated amorphous carbon, fluoropolymer, parylene, polyarylene ether, silsesquioxane, fluorinated silicon dioxide, and diamondlike carbon.--
